



ALPHA & OMEGA
SEMICONDUCTOR



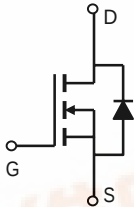
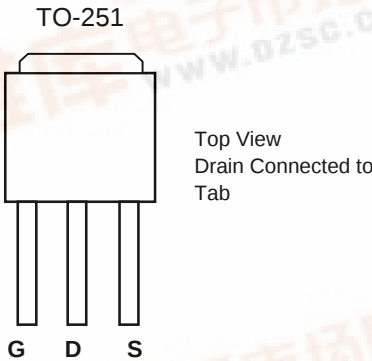
AOU400
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AOU400 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AOU400 is Pb-free (meets ROHS & Sony 259 specifications). AOU400L is a Green Product ordering option. AOU400 and AOU400L are electrically identical.*

Features

V_{DS} (V) = 60V
 I_D = 38A (V_{GS} = 10V)
 $R_{DS(ON)} < 20m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 25m\Omega$ (V_{GS} = 4.5V)



Absolute Maximum Ratings $T_A=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^B	I_D	$T_C=25^{\circ}C^G$	38
		$T_C=100^{\circ}C^B$	27
Pulsed Drain Current	I_{DM}	60	A
Avalanche Current ^C	I_{AR}	30	A
Repetitive avalanche energy $L=0.1mH^C$	E_{AR}	140	mJ
Power Dissipation ^B	P_D	$T_C=25^{\circ}C$	60
		$T_C=100^{\circ}C$	30
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	51	60	$^{\circ}C/W$
Maximum Junction-to-Case ^B	$R_{\theta JC}$	1.4	2.5	$^{\circ}C/W$

AOU400

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1	2.1	3	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	60			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		16 31	20	mΩ
		V _{GS} =4.5V, I _D =20A		20	25	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		5.6		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.74	1	V
I _S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		1920	2300	pF
C _{oss}	Output Capacitance			155		pF
C _{rss}	Reverse Transfer Capacitance			116		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.65	0.8	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =20A		47.6	68	nC
Q _{g(4.5V)}	Total Gate Charge			24.2	30	nC
Q _{gs}	Gate Source Charge			6		nC
Q _{gd}	Gate Drain Charge			14.4		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =1.5Ω, R _{GEN} =3Ω		7.4		ns
t _r	Turn-On Rise Time			5.1		ns
t _{D(off)}	Turn-Off DelayTime			28.2		ns
t _f	Turn-Off Fall Time			5.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		34	41	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		46		nC

A: The value of R_{θJA} is measured with the device in a still air environment with T_A=25°C.

B: The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

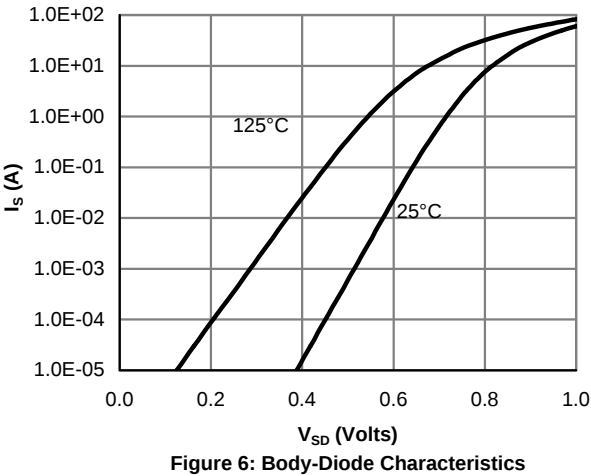
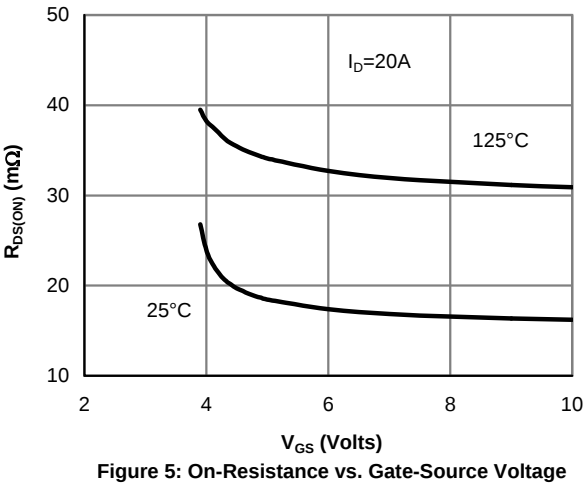
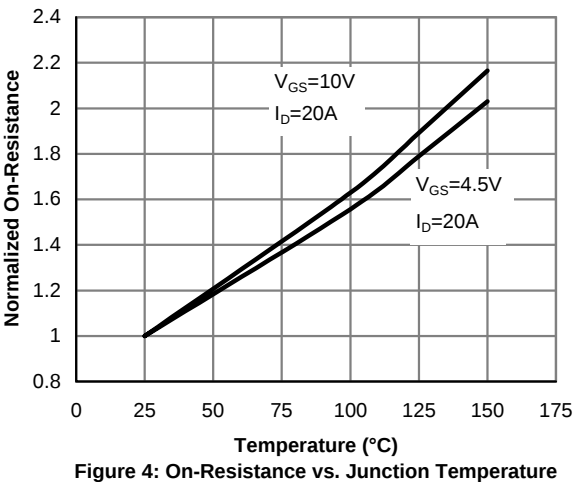
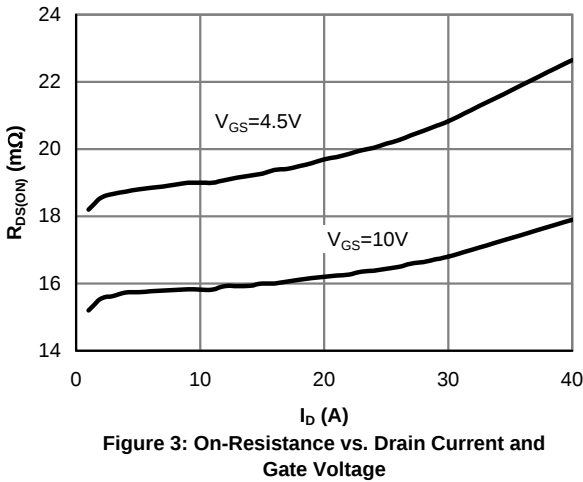
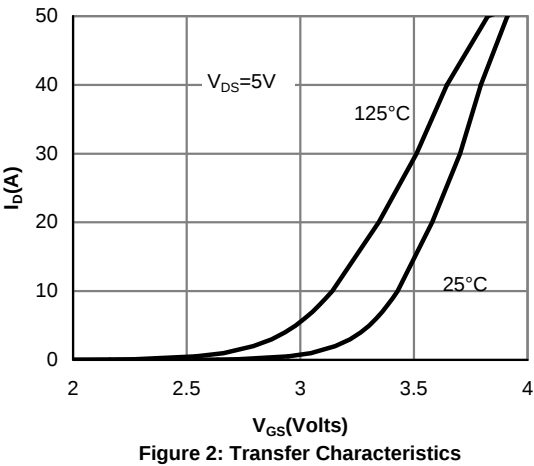
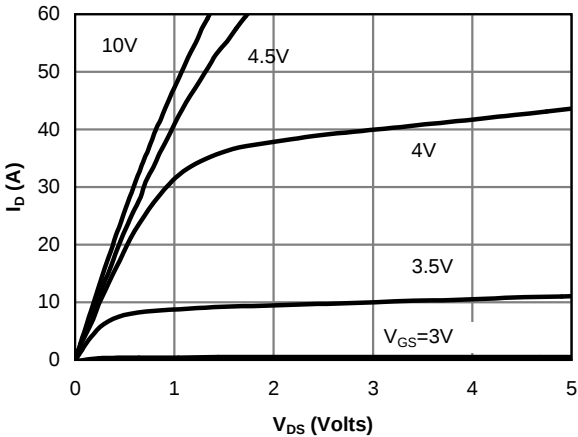
F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.

G: The maximum current rating is limited by bond-wires.

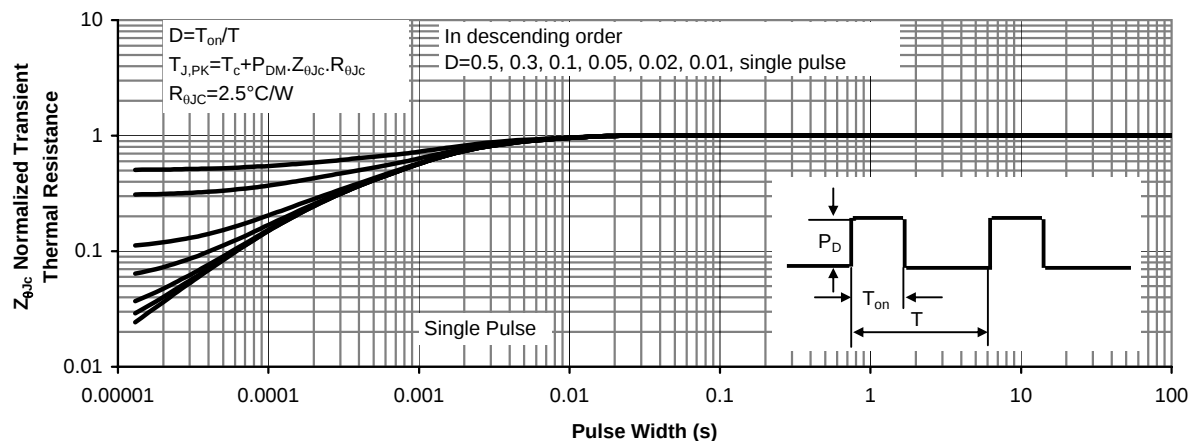
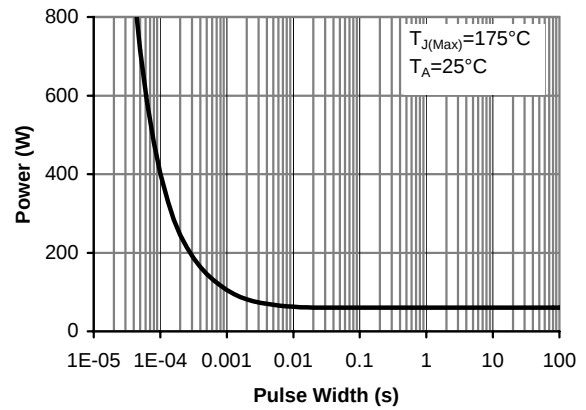
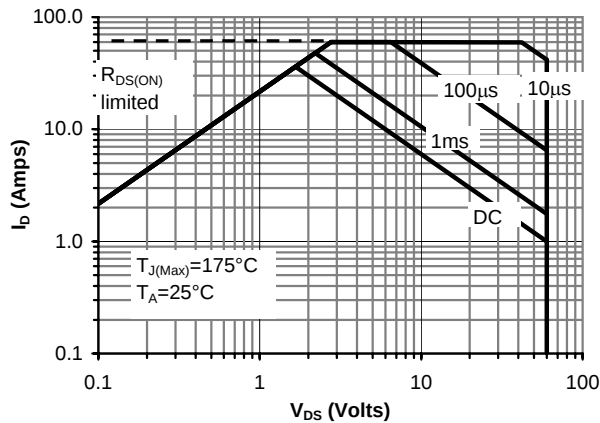
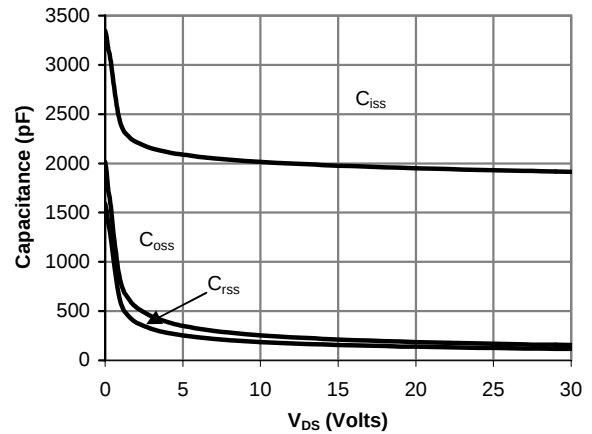
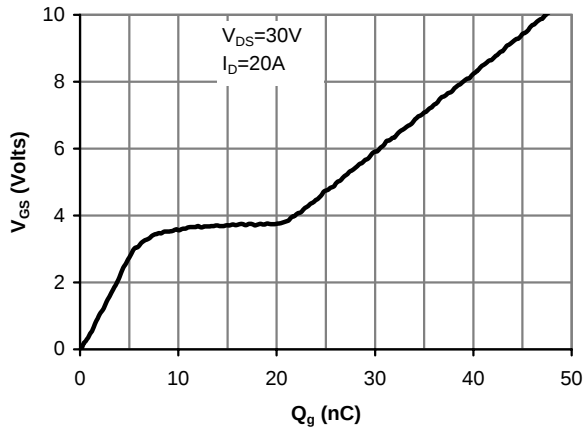
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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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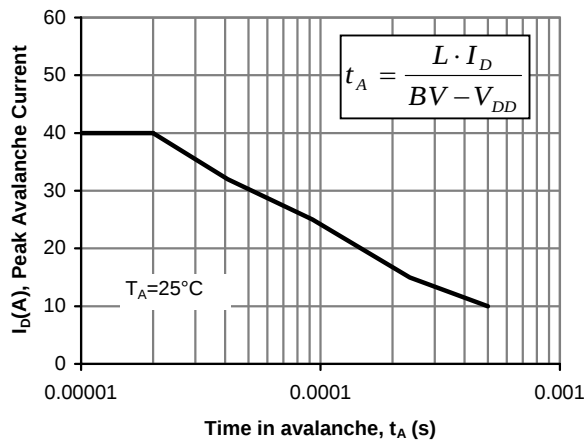


Figure 12: Single Pulse Avalanche capability

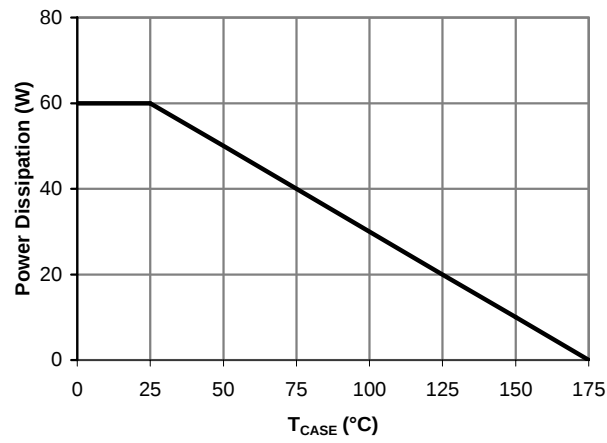


Figure 13: Power De-rating (Note B)

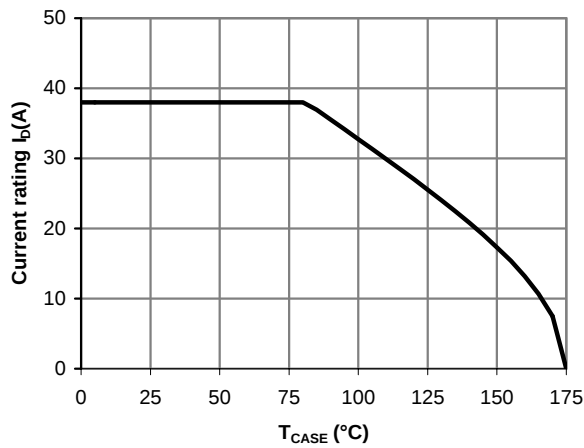


Figure 14: Current De-rating (Note B)